# Digital Transistors (BRT) R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$

# PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### **Features**

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

Rating	Symbol	Max	Unit
Collector-Base Voltage	$V_{CBO}$	50	Vdc
Collector-Emitter Voltage	$V_{CEO}$	50	Vdc
Collector Current – Continuous	I <sub>C</sub>	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	30	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	5	Vdc

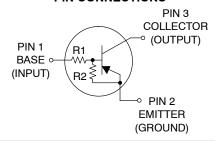
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



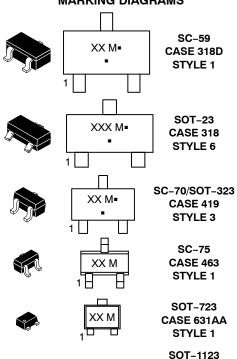
#### ON Semiconductor®

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#### **PIN CONNECTIONS**



#### **MARKING DIAGRAMS**



XXX = Specific Device Code M = Date Code\*

= Pb-Free Package
 (Note: Microdot may be in either location)

X ML 1

\*Date Code orientation may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

See detailed ordering, marking, and shipping information on page 2 of this data sheet.

CASE 524AA STYLE 1

**Table 1. ORDERING INFORMATION** 

Device	Part Marking	Package	Shipping <sup>†</sup>
MUN2133T1G	6K	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2133LT1G, NSVMMUN2133LT1G	A6K	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5133T1G, SMUN5133T1G	6K	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTA143ZET1G, NSVDTA143ZET1G	6K	SC-75 (Pb-Free)	3000 / Tape & Reel
DTA143ZM3T5G	6K	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBA143ZF3T5G	E(90°)*	SOT-1123 (Pb-Free)	8000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

 $<sup>*(</sup>XX^{\circ})$  = Degree rotation in the clockwise direction.

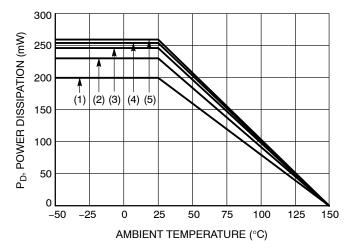


Figure 1. Derating Curve

- (1) SC-75 and SC-70/SOT-323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm<sup>2</sup>, 1 oz. copper trace
- (5) SOT-723; Minimum Pad

## **Table 2. THERMAL CHARACTERISTICS**

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC-59) (MUN2133)				•
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	230 338 1.8 2.7	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\thetaJA}$	540 370	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ heta JL}$	264 287	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-23) (MMUN2133L)	•		•	•
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	246 400 2.0 3.2	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	508 311	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ heta JL}$	174 208	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Thermal Characteristics (SC-70/SOT-323) (MUN5133)				•
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	$P_D$	202 310 1.6 2.5	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	618 403	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ heta JL}$	280 332	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Thermal Characteristics (SC-75) (DTA143ZE)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	$P_D$	200 300 1.6 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	600 400	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Thermal Characteristics (SOT-723) (DTA143ZM3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	260 600 2.0 4.8	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	480 205	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- 1. FR-4 @ Minimum Pad.
- 2. FR-4 @ 1.0 x 1.0 Inch Pad.
- 3. FR 4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air. 4. FR 4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

**Table 2. THERMAL CHARACTERISTICS** 

Characteristic		Symbol	Max	Unit
Thermal Characteristics (SOT-1123) (NSBA143ZF3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 3) (Note 4) (Note 3) (Note 4)	P <sub>D</sub>	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 3) (Note 4)	$R_{ hetaJA}$	493 421	°C/W
Thermal Resistance, Junction to Lead	(Note 3)	$R_{ hetaJL}$	193	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- 1. FR-4 @ Minimum Pad.
- 2. FR-4 @ 1.0 x 1.0 Inch Pad.
- 3. FR -4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air. 4. FR -4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					•
Collector-Base Cutoff Current (V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0)	I <sub>CBO</sub>	_	_	100	nAdc
Collector-Emitter Cutoff Current (V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	_	-	500	nAdc
Emitter-Base Cutoff Current $(V_{EB} = 6.0 \text{ V, } I_{C} = 0)$	I <sub>EBO</sub>	_	_	0.18	mAdc
Collector-Base Breakdown Voltage $(I_C = 10 \mu A, I_E = 0)$	V <sub>(BR)</sub> CBO	50	-	-	Vdc
Collector–Emitter Breakdown Voltage (Note 5) $(I_C = 2.0 \text{ mA}, I_B = 0)$	V <sub>(BR)</sub> CEO	50	_	_	Vdc
ON CHARACTERISTICS	·				
DC Current Gain (Note 5) (I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V)	h <sub>FE</sub>	80	140	_	
Collector – Emitter Saturation Voltage (Note 5) (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.3 mA)	VCE(sat)	_	_	0.25	Vdc
Input Voltage (off) $(V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A})$	V <sub>i(off)</sub>	_	0.7	0.5	Vdc
Input Voltage (on) $(V_{CE} = 0.3 \text{ V, I}_{C} = 5.0 \text{ mA})$	V <sub>i(on)</sub>	1.3	0.9	_	Vdc
Output Voltage (on) ( $V_{CC} = 5.0 \text{ V}$ , $V_B = 2.5 \text{ V}$ , $R_L = 1.0 \text{ k}\Omega$ )	V <sub>OL</sub>	_	_	0.2	Vdc
Output Voltage (off) ( $V_{CC} = 5.0 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1.0 \text{ k}\Omega$ )	V <sub>OH</sub>	4.9	_	_	Vdc
Input Resistor	R1	3.3	4.7	6.1	kΩ
Resistor Ratio	$R_1/R_2$	0.08	0.1	0.14	

<sup>5.</sup> Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# TYPICAL CHARACTERISTICS MUN2133, MMUN2133L, MUN5133, DTA143ZE, DTA143ZM3

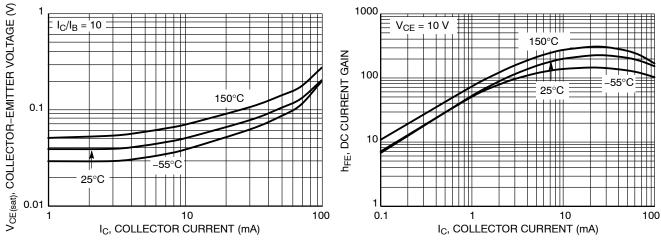


Figure 2. V<sub>CE(sat)</sub> vs. I<sub>C</sub>

Figure 3. DC Current Gain

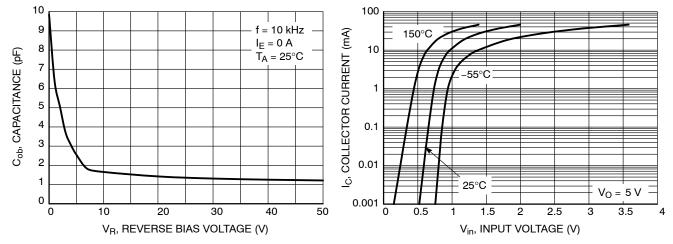


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

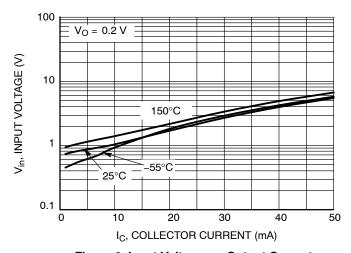


Figure 6. Input Voltage vs. Output Current

# TYPICAL CHARACTERISTICS NSBA143ZF3

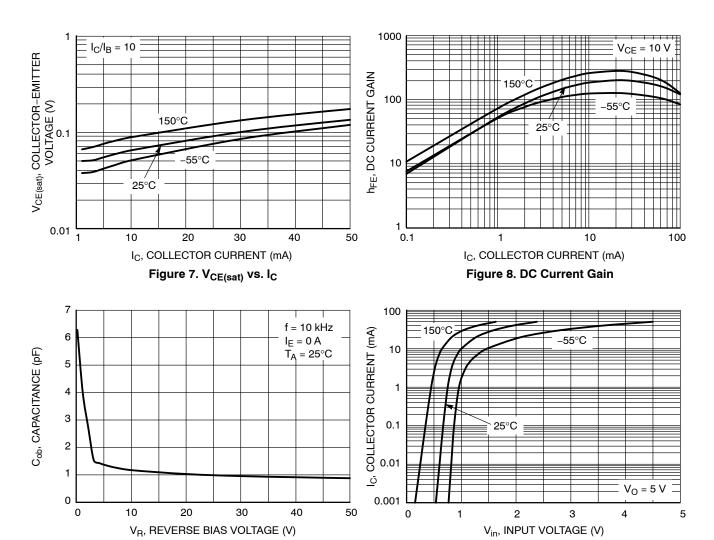


Figure 9. Output Capacitance

Figure 10. Output Current vs. Input Voltage

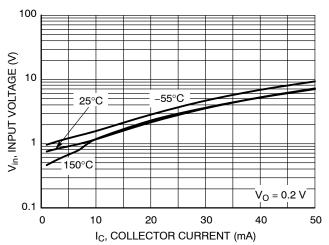


Figure 11. Input Voltage vs. Output Current

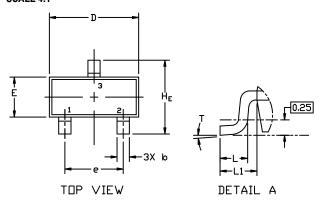


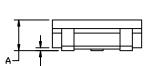


SOT-23 (TO-236) **CASE 318 ISSUE AT** 

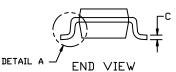
**DATE 01 MAR 2023** 

# SCALE 4:1





SIDE VIEW



#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

## **GENERIC MARKING DIAGRAM\***

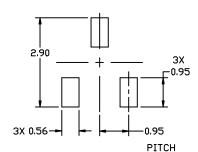


XXX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.



#### RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

#### **STYLES ON PAGE 2**

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DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 2

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#### **SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	N	
STYLE 9:	STYLE 10:	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN		PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE		2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE		3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	N PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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DESCRIPTION:	SOT-23 (TO-236)		PAGE 2 OF 2

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SCALE 2:1

SC-59 CASE 318D-04 ISSUE H

**DATE 28 JUN 2012** 

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	MOM	MAX
Α	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
С	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
е	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.80	3.00	0.099	0.110	0.118

#### **GENERIC MARKING DIAGRAM**



XXX = Specific Device Code

Μ = Date Code = Pb-Free Package\*

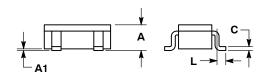
(\*Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

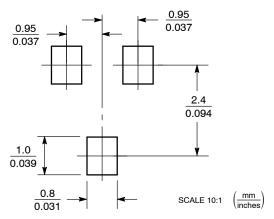
STYLE 1:		STYLE 2:		STYLE 3:	
PIN 1. BAS	SE	PIN 1.	ANODE	PIN 1.	ANODE
2. EM	ITTER	2.	N.C.	2.	ANODE
3. CO	LLECTOR	3.	CATHODE	3.	CATHODE

STYLE 4:	STYLE 5:	STYLE 6:
PIN 1. CATHODE	PIN 1. CATHODE	PIN 1. ANODE
2. N.C.	2. CATHODE	2. CATHODE
<ol><li>ANODE</li></ol>	3. ANODE	<ol><li>ANODE/CATHODE</li></ol>

# Ε $H_{E}$



### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	SC-59	•	PAGE 1 OF 1	

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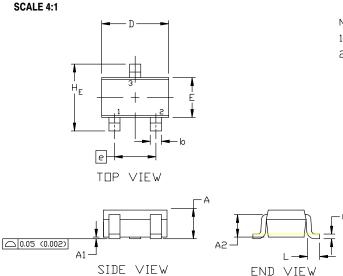
SC-70 (SOT-323) **CASE 419** ISSUE R

**DATE 11 OCT 2022** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF				0.028 BS	C
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BS	C	
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



#### **GENERIC MARKING DIAGRAM**

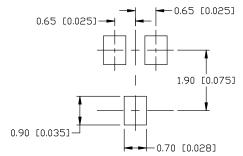


XX = Specific Device Code

М = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the IN Semiconductor Soldering and Mounting Techniques Reference Manual, SILDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	<ol><li>CATHODE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>COLLECTOR</li></ol>	3. DRAIN	<ol><li>CATHODE-ANODE</li></ol>	3. ANODE-CATHODE	<ol><li>CATHODE</li></ol>

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DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1	

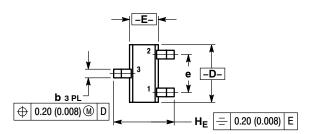
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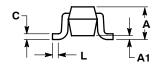




SC-75/SOT-416 CASE 463-01 **ISSUE G** 

**DATE 07 AUG 2015** 





STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR

STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE

STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS				INCHES	;
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
С	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.061	0.063	0.065
Е	0.70	0.80	0.90	0.027	0.031	0.035
Ф	1	.00 BSC	)	(	0.04 BSC	
Г	0.10	0.15	0.20	0.004	0.006	0.008
HE	1.50	1.60	1.70	0.060	0.063	0.067

#### **GENERIC MARKING DIAGRAM\***



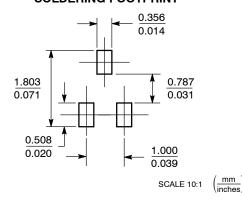
XX= Specific Device Code

Μ = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	SC-75/SOT-416		PAGE 1 OF 1	

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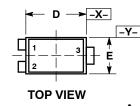




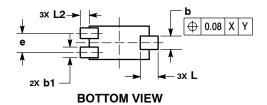
SOT-1123 CASE 524AA ISSUE C

**DATE 29 NOV 2011** 

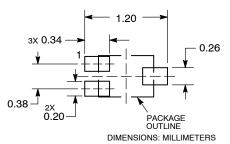
#### SCALE 8:1







#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### NOTES

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE
- MINIMUM THICKNESS OF BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD
  FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS				
DIM	MIN MAX				
Α	0.34	0.40			
b	0.15	0.28			
b1	0.10	0.20			
С	0.07	0.17			
D	0.75	0.85			
Е	0.55	0.65			
е	0.35	0.40			
HE	0.95	1.05			
L	0.185	REF			
L2	0.05	0.15			

#### **GENERIC MARKING DIAGRAM\***



= Specific Device Code

Μ = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	<ol><li>CATHODE</li></ol>	<ol><li>SOURCE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>DRAIN</li></ol>

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DESCRIPTION:	SOT-1123, 3-LEAD, 1.0X0	.6X0.37, 0.35P	PAGE 1 OF 1	

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SOT-723 CASE 631AA-01 ISSUE D

**DATE 10 AUG 2009** 

## NOTES:

- NOTES.

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.

  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD
- FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS				
DIM	MIN	NOM	MAX		
Α	0.45	0.50	0.55		
b	0.15	0.21	0.27		
b1	0.25	0.31	0.37		
С	0.07	0.12	0.17		
D	1.15	1.20	1.25		
E	0.75	0.80	0.85		
е		0.40 BS0			
ΗE	1.15	1.20	1.25		
L		0.29 REF			
L2	0.15	0.20	0.25		

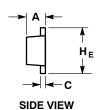
#### **GENERIC** MARKING DIAGRAM\*

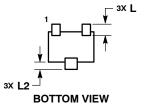


= Specific Device Code XX Μ = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

# -X-2X b ⊕ 0.08 X Y **TOP VIEW**

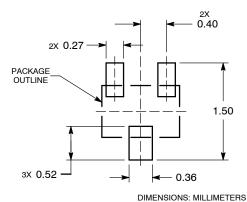




STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

**RECOMMENDED SOLDERING FOOTPRINT\*** 



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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